

**SANYO**

No.4499

**2SK2074**

N-Channel Junction Silicon FET  
 High-Frequency Low-Noise  
 Amp Applications

**Applications**

- AM tuner RF amp applications.
- Low-noise amp.

**Features**

- Large  $|Y_{fs}|$
- Small  $C_{iss}$
- Very low noise figure.

**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

		unit
Drain-to-Source Voltage	$V_{DSX}$	15 V
Gate-to-Drain Voltage	$V_{GDS}$	-15 V
Gate Current	$I_G$	10 mA
Drain Current	$I_D$	50 mA
Allowable Power Dissipation	$P_D$	300 mW
Junction Temperature	$T_j$	150 °C
Storage Temperature	$T_{stg}$	-55 to +150 °C

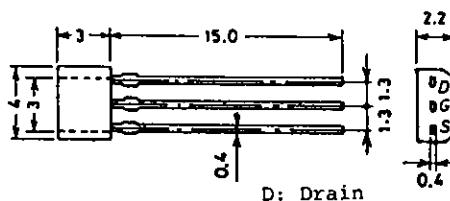
**Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

			min	typ	max	unit
G-D Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu\text{A}, V_{DS} = 0$	-15			V
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = -10\text{V}, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$V_{GS(\text{off})}$	$V_{DS} = 5\text{V}, I_D = 100\mu\text{A}$	-0.3	-0.6	-1.2	V
Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0$	6.0*	20.0*	20.0*	mA
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{kHz}$	20	30		mS
Input Capacitance	$C_{iss}$	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		9.5		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		2.7		pF
Noise Figure	NF	$V_{DS} = 5\text{V}, R_g = 1\text{k}\Omega, I_D = 1\text{mA}, f = 1\text{MHz}$		0.5		dB

\* : The 2SK2074 is classified by  $I_{DSS}$  as follows (unit : mA)

6.0	F	12.0	10.0	G	20.0
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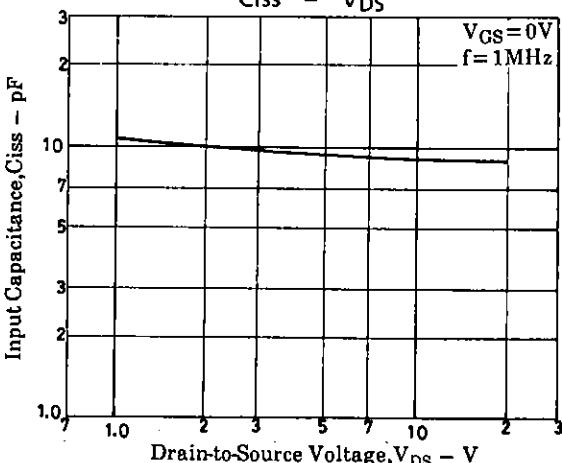
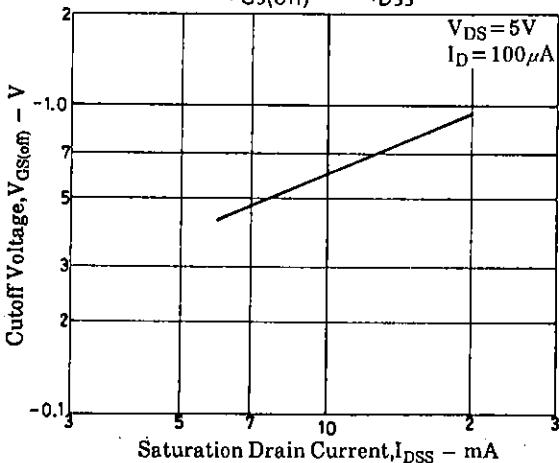
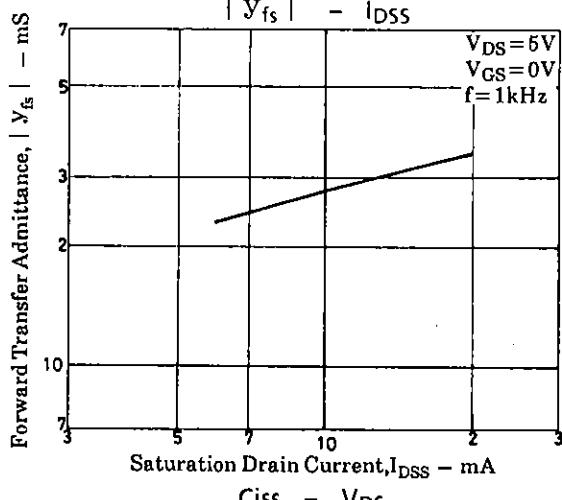
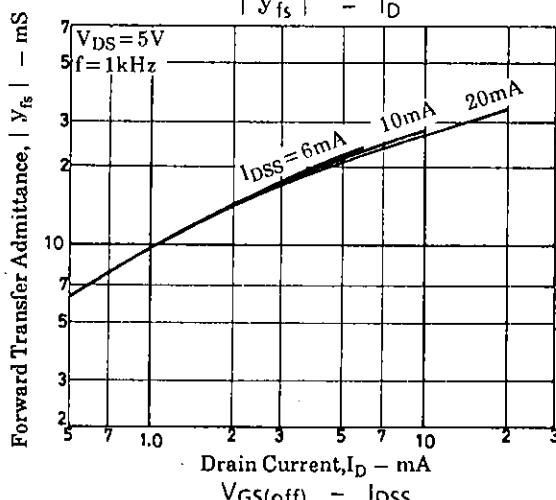
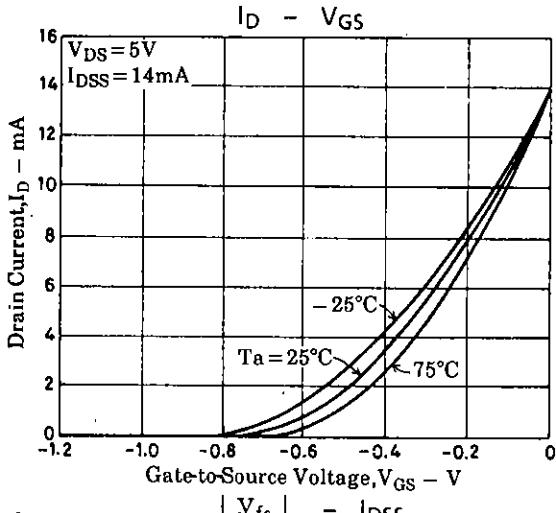
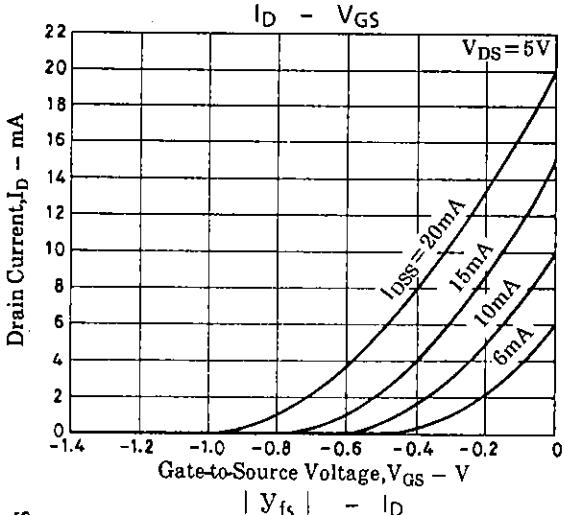
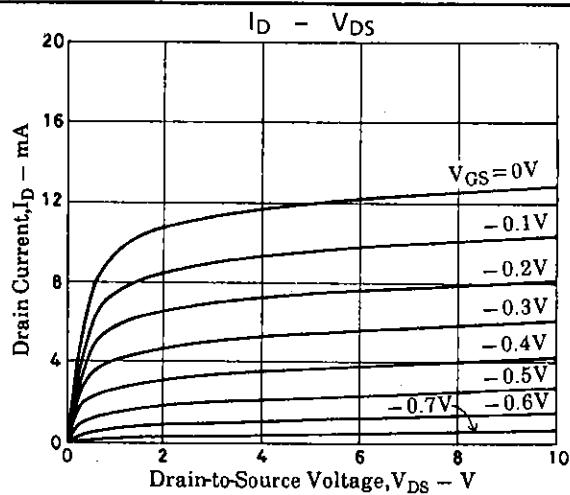
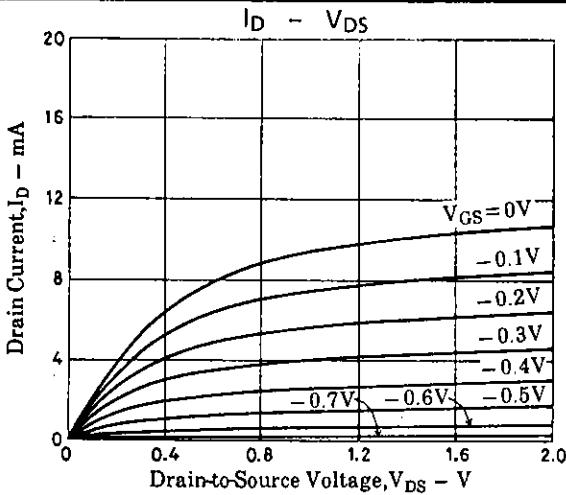
**Package Dimensions 2034**  
 (unit: mm)

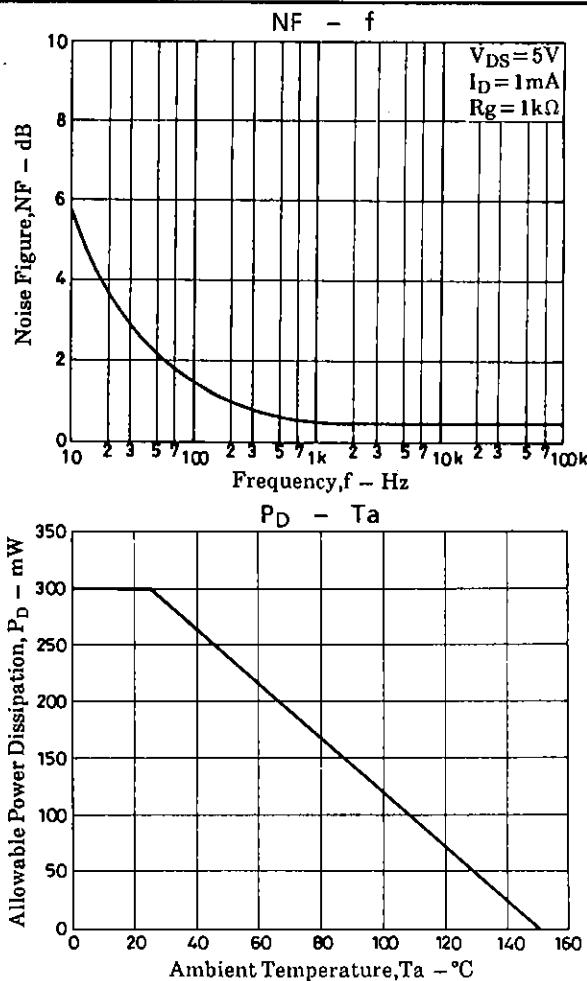
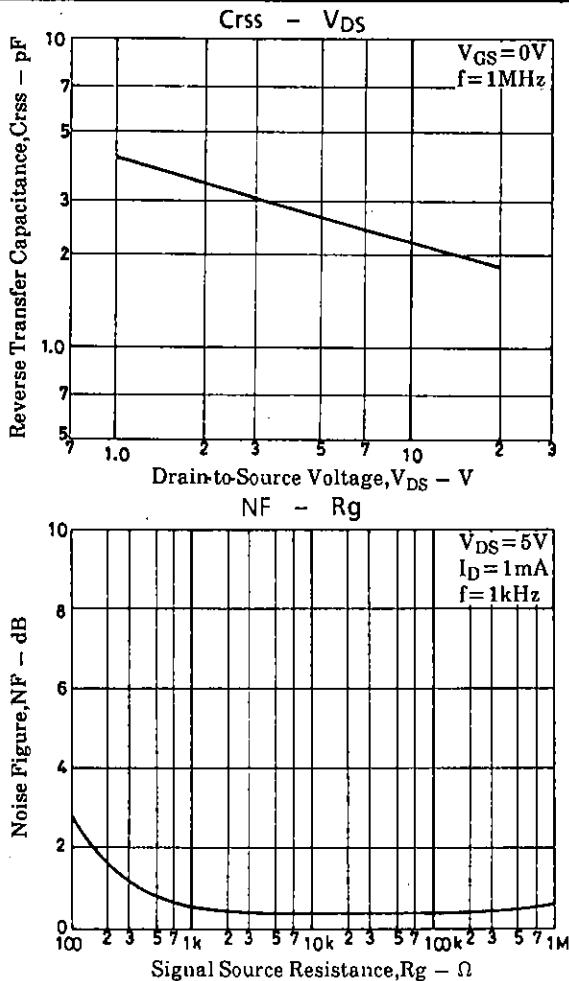


D: Drain  
 G: Gate  
 S: Source

SANYO: SPA

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